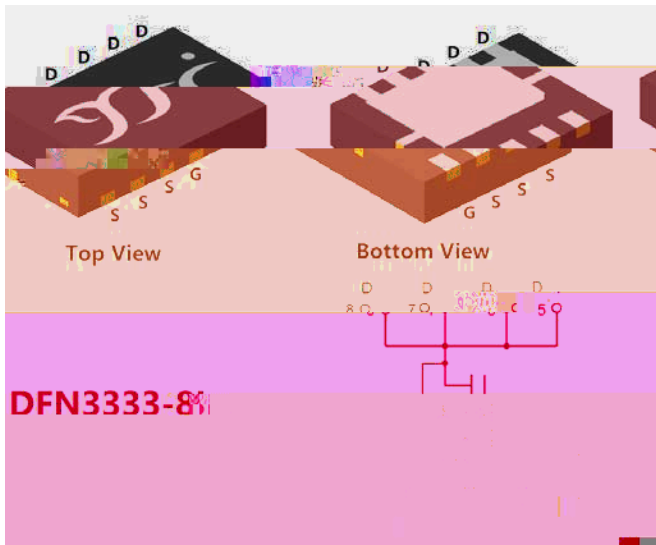


## N-Channel Enhancement Mode Field Effect Transistor



### Product Summary

$V_{DS}$	60V
$I_D$	18A

### Absolute Maximum Ratings (T

Drain Current	$T_C=25$	$I_D$	18	A
	$T_C=100$		11	
	$T_A=25$		5.7	
	$T_A=100$		3.6	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	60	A
Avalanche energy <sup>B</sup>		EAS	72	mJ

Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	$R_{JC}$	6.7	/W
		$R_{JA}$	60	/W
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 +150	

### Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ18N06AQ	F1	Q18N06A	5000	10000	100000	13" reel



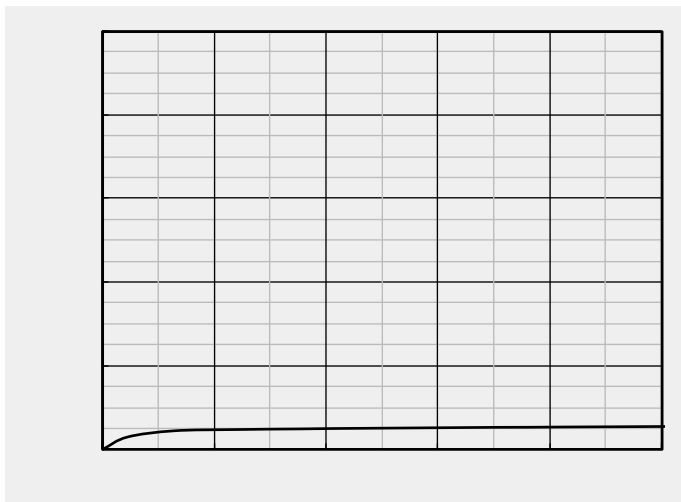
## YJQ18N06AQ

### Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max
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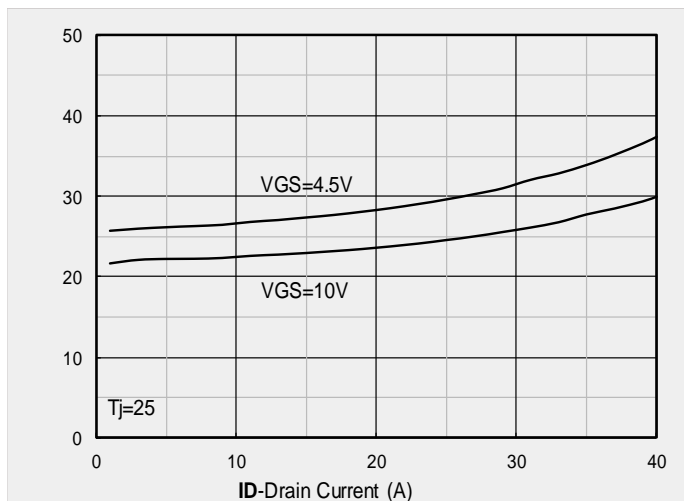


Typical Electrical and Thermal Characteristics Diagrams





# YJQ18N06AQ



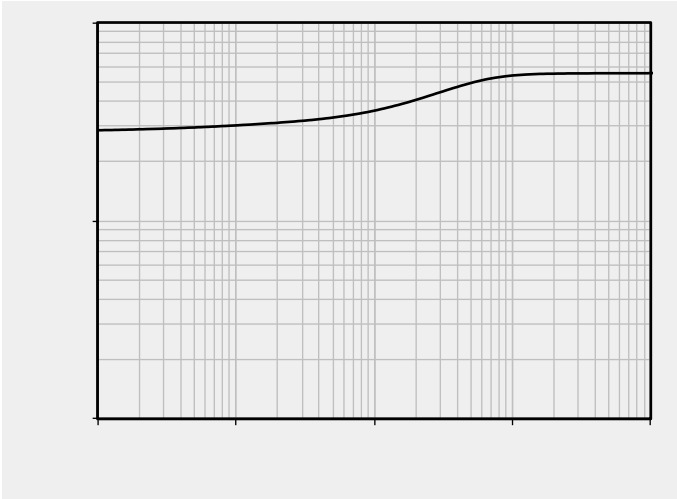


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area



DFN3333-8L Package information

Note:

1. Controlling dimension: in millimeters.



## Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of t



# YJQ18N06AQ

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Rev	Date	Modify content
1.0	30-Jun-23	New datasheet